



IPC042N03L3X1SA1 Information

Heisener.com

Part Number IPC042N03L3X1SA1

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 30V SAWN BARE DIE

Package Die

For the pricing/inventory/lead time, please contact

us

For Reference Only

Website: https://www.heisener.com
E-mail: salesdept@heisener.com



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Certified Quality

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IPC042N03L3X1SA1 Specifications

Manufacturer Part NumberIPC042N03L3X1SA1ManufacturerInfineon TechnologiesCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageDieSeriesOptiMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C1A (Tj)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.2V @ 250μAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds-Vgs (Max)-FET Feature-Power Dissipation (Max)-Rds On (Max) @ Id, Vgs50 mOhm @ 2A, 10VOperating Temperature-Mounting TypeSurface MountSupplier Device PackageSawn on foilPackage / CaseDie		
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Transistors - FETs, MOSFETs - Single Package Die OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 1A (Τj) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) - FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature - Mounting Type Surface Mount Supplier Device Package Package / Case Die	Manufacturer	Infineon Technologies
PackageDieSeriesOptiMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C1A (Tj)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.2V @ 250μAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds-Vgs (Max)-FET Feature-Power Dissipation (Max)-Rds On (Max) @ Id, Vgs50 mOhm @ 2A, 10VOperating Temperature-Mounting TypeSurface MountSupplier Device PackageSawn on foilPackage / CaseDie	Category	Discrete Semiconductor Products
SeriesOptiMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C1A (Tj)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.2V @ 250μAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds-Vgs (Max)-FET Feature-Power Dissipation (Max)-Rds On (Max) @ Id, Vgs50 mOhm @ 2A, 10VOperating Temperature-Mounting TypeSurface MountSupplier Device PackageSawn on foilPackage / CaseDie		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C1A (Tj)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.2V @ 250μAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds-Vgs (Max)-FET Feature-Power Dissipation (Max)-Rds On (Max) @ Id, Vgs50 mOhm @ 2A, 10VOperating Temperature-Mounting TypeSurface MountSupplier Device PackageSawn on foilPackage / CaseDie	Package	Die
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 1A (Tj) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) - FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 50 mOhm @ 2A, 10V Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case MOSFET (Metal Oxide) 30V MOSFET (Metal Oxide) 30V 1A (Tj)	Series	OptiMOS?
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 1A (Tj) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case 30V 1A (Tj) 1A (Tj	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) - FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 50 mOhm @ 2A, 10V Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case Die	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) - FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case A 2.2V @ 250μA	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 50 mOhm @ 2A, 10V Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case Die	Current - Continuous Drain (Id) @ 25°C	1A (Tj)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) - FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 50 mOhm @ 2A, 10V Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case Die	Vgs(th) (Max) @ Id	2.2V @ 250μA
Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 50 mOhm @ 2A, 10V Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case Die	Gate Charge (Qg) (Max) @ Vgs	-
FET Feature - Power Dissipation (Max) - Rds On (Max) @ Id, Vgs 50 mOhm @ 2A, 10V Operating Temperature - Mounting Type Surface Mount Supplier Device Package Sawn on foil Package / Case Die	Input Capacitance (Ciss) (Max) @ Vds	-
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 50 mOhm @ 2A, 10V Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case Die	Vgs (Max)	-
Rds On (Max) @ Id, Vgs 50 mOhm @ 2A, 10V Operating Temperature - Mounting Type Surface Mount Supplier Device Package Sawn on foil Package / Case Die	FET Feature	-
Operating Temperature - Mounting Type Surface Mount Supplier Device Package Sawn on foil Package / Case Die	Power Dissipation (Max)	-
Mounting Type Surface Mount Supplier Device Package Sawn on foil Package / Case Die	Rds On (Max) @ Id, Vgs	50 mOhm @ 2A, 10V
Supplier Device Package Sawn on foil Package / Case Die	Operating Temperature	-
Package / Case Die	Mounting Type	Surface Mount
-	Supplier Device Package	Sawn on foil
Report errors?	Package / Case	Die
		Report errors?

IPC042N03L3X1SA1 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IPC042N03L3X1SA1 Payment Methods





















IPC042N03L3X1SA1 Shipping Methods













If you have any question about IPC042N03L3X1SA1, please do not hesitate to contact us!

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